

Title (en)  
HALF-BRIDGE HAVING POWER SEMICONDUCTORS

Title (de)  
HALBBRÜCKE MIT LEISTUNGSHALBLEITERN

Title (fr)  
DEMI-PONT AYANT SEMI-CONDUCTEURS DE PUISSANCE

Publication  
**EP 3738200 A1 20201118 (DE)**

Application  
**EP 18710367 A 20180227**

Priority  
EP 2018054788 W 20180227

Abstract (en)  
[origin: WO2019166072A1] The invention relates to a half-bridge (102) comprising a first and second power semiconductor (108, 110, S1, S2, S3, S4) connected in series, a controller (120) for the power semiconductors (108, 110, S1, S2, S3, S4), a line which originates from the connecting node (112) of the power semiconductors (108, 110, S1, S2, S3, S4), an apparatus (130) for measuring the current in the line, wherein the controller (120) is configured to compare the current with an upper and a lower threshold value (132, 134), to switch off the first power semiconductor (108, 110, S1, S2, S3, S4) when the upper threshold value (132) is reached, and, following the expiry of a first dead time (210), to switch on the second power semiconductor (108, 110, S1, S2, S3, S4), and to switch off the second power semiconductor (108, 110, S1, S2, S3, S4) when the lower threshold value (134) is reached, and, following the expiry of a second dead time (212), to switch on the first power semiconductor (108, 110, S1, S2, S3, S4).

IPC 8 full level  
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Citation (search report)  
See references of WO 2019166072A1

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DOCDB simple family (publication)  
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